

N-channel 40 V, 1.4 mΩ standard level MOSFET in LFPAK56E 5 July 2018 Product data sheet

### 1. General description

Automotive qualified N-channel MOSFET using the latest Trench 9 low ohmic superjunction technology, housed in an enhanced LFPAK56E package. This product has been fully designed and qualified to meet AEC-Q101 requirements delivering high performance and endurance.

### 2. Features and benefits

- Fully automotive qualified to AEC-Q101:
  - 175 °C rating suitable for thermally demanding environments
- Trench 9 Superjunction technology:
  - Reduced cell pitch enables enhanced power density and efficiency with lower  $R_{\text{DSon}}$  in same footprint
  - Improved SOA and avalanche capability compared to standard TrenchMOS
  - Tight V<sub>GS(th)</sub> limits enable easy paralleling of MOSFETs
- LFPAK Gull Wing leads:
  - High Board Level Reliability absorbing mechanical stress during thermal cycling, unlike traditional QFN packages
  - · Visual (AOI) soldering inspection, no need for expensive x-ray equipment
  - Easy solder wetting for good mechanical solder joint
- LFPAK copper clip technology:
  - Improved reliability, with reduced R<sub>th</sub> and R<sub>DSon</sub>
  - · Increases maximum current capability and improved current spreading

### 3. Applications

- 12 V automotive systems
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- Ultra high performance power switching

### 4. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	-	40	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	-	190	А
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	-	395	W

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#### N-channel 40 V, 1.4 mΩ standard level MOSFET in LFPAK56E

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static chara	Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11		0.74	1.06	1.4	mΩ	
Dynamic ch	aracteristics							
$Q_{GD}$	gate-drain charge	I <sub>D</sub> = 25 A; V <sub>DS</sub> = 32 V; V <sub>GS</sub> = 10 V; Fig. 13; Fig. 14		-	13	27	nC	
Source-drai	n diode							
Q <sub>r</sub>	recovered charge	$    I_{S} = 25 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\ \text{V}_{DS} = 20 \text{ V}                                  $		-	39	-	nC	
S	softness factor	$    I_{S} = 25 \text{ A}; dI_{S}/dt = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V}; \\     V_{DS} = 20 \text{ V}; \text{ T}_{j} = 25 ^{\circ}\text{C} $		-	0.7	-		

[1] 190A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

# 5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	S	source	recel	D
2	S	source		
3	S	source		G
4	G	gate		mbb076 S
mb	D	mounting base; connected to drain		
			LFPAK56E; Power- SO8 (SOT1023)	

### 6. Ordering information

### Table 3. Ordering information

Type number	Package	Package					
	Name	Description	Version				
BUK7J1R4-40H	LFPAK56E; Power-SO8	plastic, single-ended surface-mounted package (LFPAK56); 4 leads; 1.27 mm pitch	SOT1023				

### 7. Marking

Table 4. Marking codes	
Type number	Marking code
BUK7J1R4-40H	71H440

#### N-channel 40 V, 1.4 mΩ standard level MOSFET in LFPAK56E

### 8. Limiting values

#### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V <sub>DS</sub>	drain-source voltage	25 °C ≤ T <sub>j</sub> ≤ 175 °C		-	40	V
V <sub>GS</sub>	gate-source voltage	DC; T <sub>j</sub> ≤ 175 °C		-10	20	V
P <sub>tot</sub>	total power dissipation	T <sub>mb</sub> = 25 °C; <u>Fig. 1</u>		-	395	W
I <sub>D</sub>	drain current	V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 25 °C; <u>Fig. 2</u>	[1]	-	190	А
		V <sub>GS</sub> = 10 V; T <sub>mb</sub> = 100 °C; <u>Fig. 2</u>	[1]	-	190	А
I <sub>DM</sub>	peak drain current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$ ; Fig. 3		-	600	А
T <sub>stg</sub>	storage temperature			-55	175	°C
Tj	junction temperature			-55	175	°C
Source-drai	n diode					
I <sub>S</sub>	source current	T <sub>mb</sub> = 25 °C	[2]	-	145	А
I <sub>SM</sub>	peak source current	pulsed; $t_p \le 10 \ \mu s$ ; $T_{mb} = 25 \ ^{\circ}C$		-	600	А
Avalanche r	uggedness					
E <sub>DS(AL)S</sub>	non-repetitive drain- source avalanche energy	$\label{eq:loss} \begin{array}{l} I_D = 190 \text{ A};  V_{sup} \leq 40 \text{ V};  \text{R}_{GS} = 50  \Omega; \\        $	[3] [4]	-	154	mJ

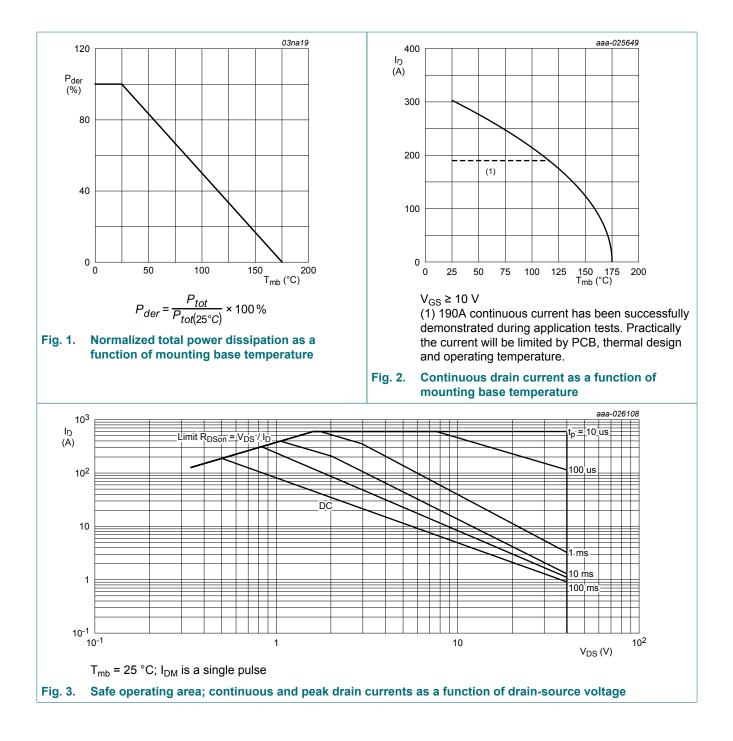
[1] 190A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

[2] 145A continuous current has been successfully demonstrated during application tests. Practically the current will be limited by PCB, thermal design and operating temperature.

[3] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

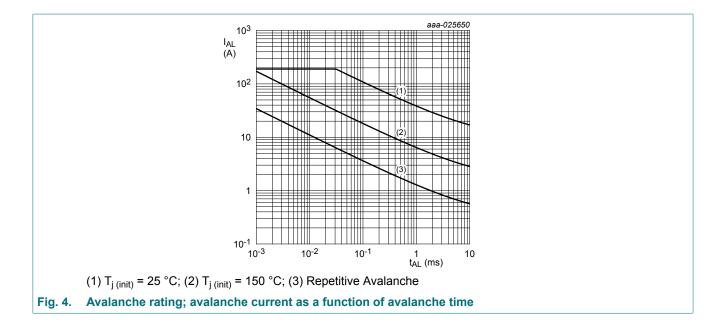
[4] Refer to application note AN10273 for further information.

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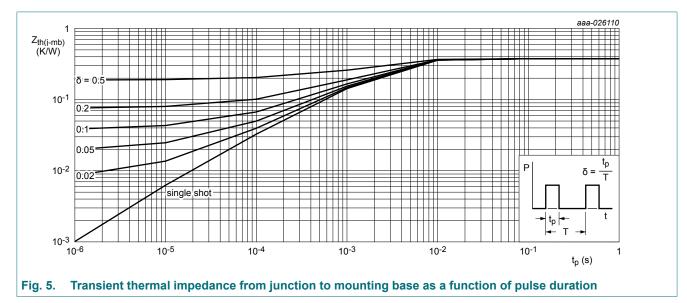
### N-channel 40 V, 1.4 mΩ standard level MOSFET in LFPAK56E



## 9. Thermal characteristics

#### **Table 6. Thermal characteristics**

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	<u>Fig. 5</u>	-	0.29	0.38	K/W



### N-channel 40 V, 1.4 m $\Omega$ standard level MOSFET in LFPAK56E

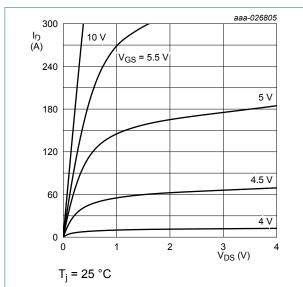
# **10. Characteristics**

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	40	42	-	V
. ,	breakdown voltage	I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -40 °C	-	39.6	-	V
		I <sub>D</sub> = 250 μA; V <sub>GS</sub> = 0 V; T <sub>j</sub> = -55 °C	36	38.9	-	V
V <sub>GS(th)</sub>	gate-source threshold voltage	I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 25 °C; <u>Fig. 9;</u> Fig. 10	2.4	3	3.6	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = -55 °C; <u>Fig. 9</u>	-	-	4.3	V
		I <sub>D</sub> = 1 mA; V <sub>DS</sub> =V <sub>GS</sub> ; T <sub>j</sub> = 175 °C; <u>Fig. 9</u>	1	-	-	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	0.1	1	μA
		V <sub>DS</sub> = 16 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 125 °C	-	2.4	10	μA
		V <sub>DS</sub> = 40 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 175 °C	-	240	500	μA
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = 20 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
		V <sub>GS</sub> = -10 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	2	100	nA
R <sub>DSon</sub>	drain-source on-state resistance	V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 25 °C; Fig. 11	0.74	1.06	1.4	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 105 °C; Fig. 12	1.05	1.57	2.23	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 125 °C; Fig. 12	1.16	1.74	2.45	mΩ
		V <sub>GS</sub> = 10 V; I <sub>D</sub> = 25 A; T <sub>j</sub> = 175 °C; Fig. 12	1.46	2.18	3.05	mΩ
R <sub>G</sub>	gate resistance	f = 1 MHz; T <sub>j</sub> = 25 °C	0.4	1	2.5	Ω
Dynamic ch	naracteristics		I			
Q <sub>G(tot)</sub>	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 32 \text{ V}; V_{GS} = 10 \text{ V};$	-	73	103	nC
Q <sub>GS</sub>	gate-source charge	Fig. 13; Fig. 14	-	21	32	nC
Q <sub>GD</sub>	gate-drain charge	1 1	-	13	27	nC
C <sub>iss</sub>	input capacitance	V <sub>DS</sub> = 25 V; V <sub>GS</sub> = 0 V; f = 1 MHz;	-	5436	7610	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C; <u>Fig. 15</u>	-	1314	1840	pF
C <sub>rss</sub>	reverse transfer capacitance		-	238	524	pF
t <sub>d(on)</sub>	turn-on delay time	V <sub>DS</sub> = 30 V; R <sub>L</sub> = 1.2 Ω; V <sub>GS</sub> = 10 V;	-	19	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 5 \Omega$	-	17	-	ns
t <sub>d(off)</sub>	turn-off delay time	1	-	43	-	ns
t <sub>f</sub>	fall time	1	-	21	-	ns
Source-dra	in diode	1	I			
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = 25 A; V <sub>GS</sub> = 0 V; T <sub>i</sub> = 25 °C; <u>Fig. 16</u>	-	0.8	1.2	V

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### N-channel 40 V, 1.4 mΩ standard level MOSFET in LFPAK56E

Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
t <sub>rr</sub>	reverse recovery time	$I_{S} = 25 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	37	-	ns
Qr	recovered charge	V <sub>DS</sub> = 20 V	-	39	-	nC
S	softness factor	$I_{S}$ = 25 A; dI <sub>S</sub> /dt = -100 A/µs; V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 20 V; T <sub>j</sub> = 25 °C	-	0.7	-	
		$\label{eq:IS} \begin{array}{l} I_{\rm S} = 25 \; \text{A}; \; \text{dI}_{\rm S}/\text{dt} = -500 \; \text{A}/\mu\text{s}; \; \text{V}_{\rm GS} = 0 \; \text{V}; \\ \text{V}_{\rm DS} = 20 \; \text{V}; \; \text{T}_{\rm j} = 25 \; ^{\circ}\text{C} \end{array}$	-	0.56	-	



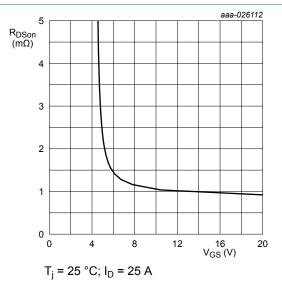


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

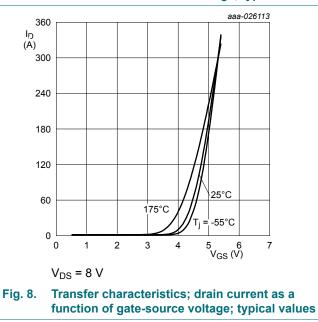
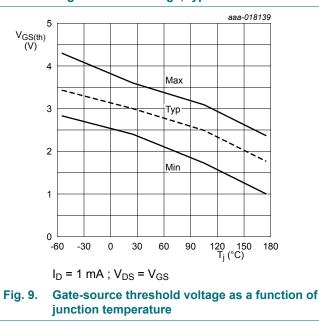
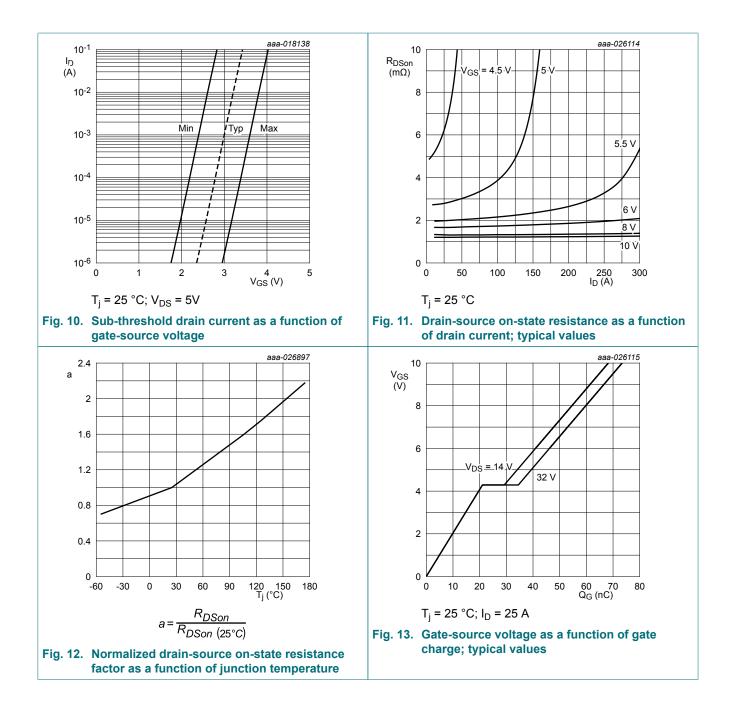


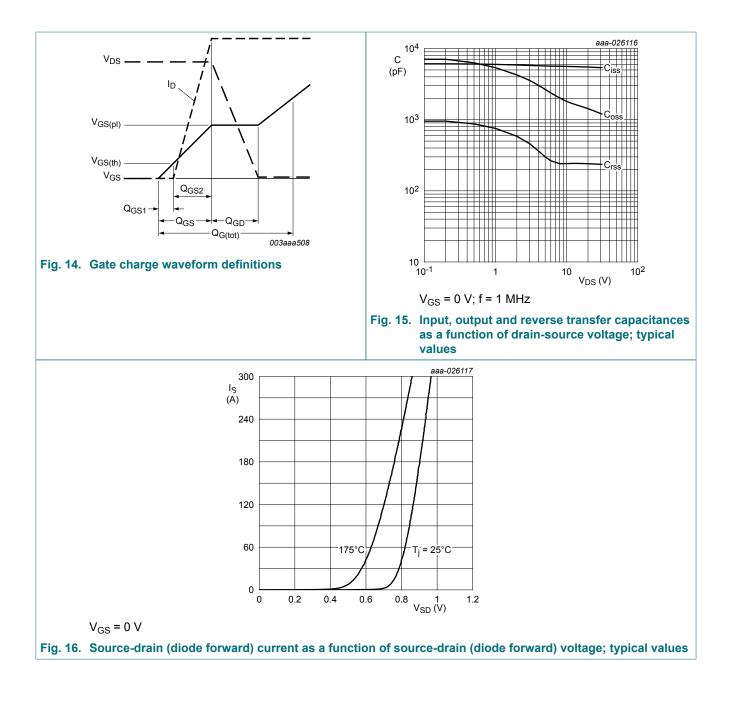
Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values



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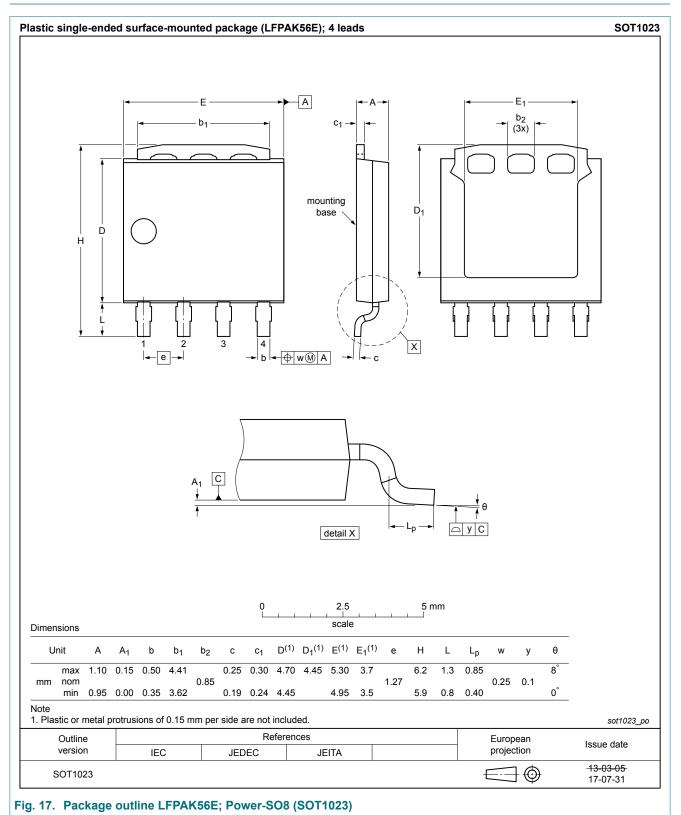


### N-channel 40 V, 1.4 mΩ standard level MOSFET in LFPAK56E



N-channel 40 V, 1.4 mΩ standard level MOSFET in LFPAK56E

### 11. Package outline



BUK7J1R4-40H

#### N-channel 40 V, 1.4 mΩ standard level MOSFET in LFPAK56E

### 12. Legal information

#### Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

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